

## 1. Description

BL7N65B, the silicon N-channel Enhanced MOSFETs, is obtained by advanced MOSFET technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. The transistor is suitable device for SMPS, high speed switching and general purpose applications.

### KEY CHARACTERISTICS

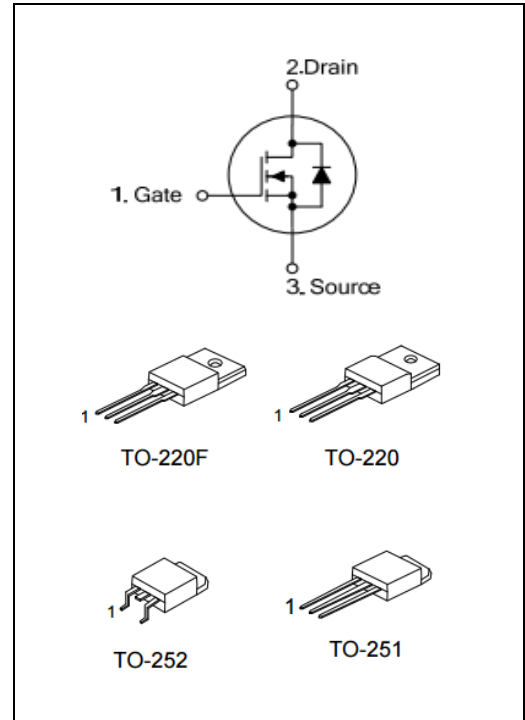
| Parameter        | Value | Unit     |
|------------------|-------|----------|
| $V_{DS@Tj,max}$  | 700   | V        |
| $I_D$            | 7     | A        |
| $R_{DS(ON).Typ}$ | 1.0   | $\Omega$ |

### FEATURES

- Fast Switching
- Low  $C_{rss}$
- 100% avalanche tested
- Improved dv/dt capability
- RoHS product

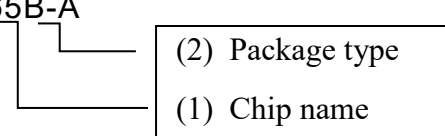
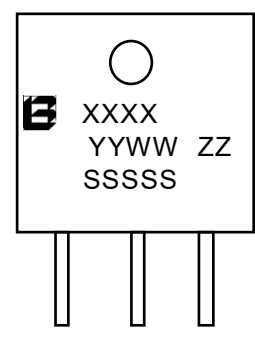
### APPLICATIONS

- High frequency switching mode power supply



## ORDERING INFORMATION

| Ordering Codes | Package | Product Code | Packing   |
|----------------|---------|--------------|-----------|
| BL7N65B-P      | TO-220  | 7N65B        | Tube      |
| BL7N65B-A      | TO-220F |              | Tube      |
| BL7N65B-U      | TO-251  |              | Tube      |
| BL7N65B-D      | TO-252  |              | Tape Reel |

|                                                                                                                                                                                                                           |                                                                                                                                                                                                                                    |
|---------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| <p><b>BL7N65B-A</b></p>  <p>(1) BL7N65B:650V 7A<br/>                 (2) A:TO-220F P:TO-220<br/>                 U:TO-251 D:TO-252</p> |  <p>XXXX: Product Code<br/>                 YYWW: Year&amp;Week<br/>                 ZZ: Assembly Code<br/>                 SSSS: Lot Code</p> |
|---------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|

## 2. ABSOLUTE RATINGS

 at  $T_C = 25^{\circ}\text{C}$ , unless otherwise specified

| Symbol         | Parameter                                            | Rating              | Units                 |
|----------------|------------------------------------------------------|---------------------|-----------------------|
| $V_{DS}$       | Drain-to-Source Voltage                              | 650                 | V                     |
| $I_D$          | Continuous Drain Current                             | 7                   | A                     |
|                | Continuous Drain Current $T_C = 100^{\circ}\text{C}$ | 4.4                 | A                     |
| $I_{DM}$       | Pulsed Drain Current(Note1)                          | 28                  | A                     |
| $V_{GS}$       | Gate-to-Source Voltage                               | $\pm 30$            | V                     |
| $E_{AS}$       | Single Pulse Avalanche Energy(Note2)                 | 400                 | mJ                    |
| $dv/dt$        | Peak Diode Recovery $dv/dt$ (Note3)                  | 5.0                 | V/ns                  |
| $P_D$          | Power Dissipation<br>No FullPAK                      | 148                 | W                     |
|                | Derating Factor above $25^{\circ}\text{C}$           | 1.13                | W/ $^{\circ}\text{C}$ |
| $P_D$          | Power Dissipation<br>FullPAK                         | 42                  | W                     |
|                | Derating Factor above $25^{\circ}\text{C}$           | 0.33                | W/ $^{\circ}\text{C}$ |
| $T_J, T_{stg}$ | Operating Junction and Storage Temperature Range     | 150, $-55$ to $150$ | $^{\circ}\text{C}$    |
| $T_L$          | Maximum Temperature for Soldering                    | 300                 | $^{\circ}\text{C}$    |

## 3. Thermal characteristics

### Thermal characteristics No FullPAK

| Symbol          | Parameter           | RATINGS | Units                       |
|-----------------|---------------------|---------|-----------------------------|
| $R_{\theta JC}$ | Junction-to-Case    | 0.88    | $^{\circ}\text{C}/\text{W}$ |
| $R_{\theta JA}$ | Junction-to-Ambient | 62.5    | $^{\circ}\text{C}/\text{W}$ |

### Thermal characteristics FullPAK

| Symbol          | Parameter           | RATINGS | Units                       |
|-----------------|---------------------|---------|-----------------------------|
| $R_{\theta JC}$ | Junction-to-Case    | 3       | $^{\circ}\text{C}/\text{W}$ |
| $R_{\theta JA}$ | Junction-to-Ambient | 62.5    | $^{\circ}\text{C}/\text{W}$ |

## 4. Electrical Characteristics

 at  $T_C = 25^\circ\text{C}$ , unless otherwise specified

| OFF Characteristics          |                                   |                                                             |        |      |      |                    |
|------------------------------|-----------------------------------|-------------------------------------------------------------|--------|------|------|--------------------|
| Symbol                       | Parameter                         | Test Conditions                                             | Values |      |      | Units              |
|                              |                                   |                                                             | Min.   | Typ. | Max. |                    |
| $V_{DSS}$                    | Drain to Source Breakdown Voltage | $V_{GS}=0V$ ,<br>$I_D=250\mu A$                             | 650    | --   | --   | V                  |
| $\Delta BV_{DSS}/\Delta T_J$ | Bvdss Temperature Coefficient     | $I_D=250\mu A$ ,<br>Reference $25^\circ\text{C}$            | --     | 0.65 | --   | $V/^\circ\text{C}$ |
| $I_{DSS}$                    | Drain to Source Leakage Current   | $V_{DS}=650V$ ,<br>$V_{GS}=0V$ ,<br>$T_J=25^\circ\text{C}$  | --     | --   | 1    | $\mu A$            |
|                              |                                   | $V_{DS}=520V$ ,<br>$V_{GS}=0V$ ,<br>$T_J=125^\circ\text{C}$ | --     | --   | 100  | $\mu A$            |
| $I_{GSS(F)}$                 | Gate to Source Forward Leakage    | $V_{GS}=+30V$                                               | --     | --   | 100  | nA                 |
| $I_{GSS(R)}$                 | Gate to Source Reverse Leakage    | $V_{GS}=-30V$                                               | --     | --   | -100 | nA                 |

| ON Characteristics |                               |                                             |        |      |      |          |
|--------------------|-------------------------------|---------------------------------------------|--------|------|------|----------|
| Symbol             | Parameter                     | Test Conditions                             | Values |      |      | Units    |
|                    |                               |                                             | Min.   | Typ. | Max. |          |
| $R_{DS(ON)}$       | Drain-to-Source On-Resistance | $V_{GS}=10V$ ,<br>$I_D=3.5A$ (Note4)        | --     | 1.0  | 1.25 | $\Omega$ |
| $V_{GS(TH)}$       | Gate Threshold Voltage        | $V_{DS}=V_{GS}$ ,<br>$I_D=250\mu A$ (Note4) | 2.0    | --   | 4.0  | V        |
| $g_{fs}$           | Forward Transconductance      | $V_{DS}=15V$ ,<br>$I_D=3.5A$ (Note4)        | --     | 11   | --   | S        |

| Dynamic Characteristics |                              |                                                  |        |      |      |          |
|-------------------------|------------------------------|--------------------------------------------------|--------|------|------|----------|
| Symbol                  | Parameter                    | Test Conditions                                  | Values |      |      | Units    |
|                         |                              |                                                  | Min.   | Typ. | Max. |          |
| $R_g$                   | Gate resistance              | $f=1.0\text{MHz}$                                | --     | 2.5  | --   | $\Omega$ |
| $C_{iss}$               | Input Capacitance            | $V_{GS}=0V$<br>$V_{DS}=25V$<br>$f=1.0\text{MHz}$ | --     | 1230 | --   | PF       |
| $C_{oss}$               | Output Capacitance           |                                                  | --     | 90   | --   |          |
| $C_{rss}$               | Reverse Transfer Capacitance |                                                  | --     | 2.6  | --   |          |

**Switching Characteristics**

| Symbol       | Parameter                      | Test Conditions                   | Values |      |      | Units |
|--------------|--------------------------------|-----------------------------------|--------|------|------|-------|
|              |                                |                                   | Min.   | Typ. | Max. |       |
| $t_{d(ON)}$  | Turn-on Delay Time             | ID =7A<br>VDD = 325V<br>VGS = 10V | --     | 31   | --   | ns    |
| $t_r$        | Rise Time                      |                                   | --     | 20   | --   |       |
| $t_{d(OFF)}$ | Turn-Off Delay Time            |                                   | --     | 78   | --   |       |
| $t_f$        | Fall Time                      |                                   | --     | 28   | --   |       |
| $Q_g$        | Total Gate Charge              | ID =7A<br>VDD =520V<br>VGS = 10V  | --     | 22   | --   | nC    |
| $Q_{gs}$     | Gate to Source Charge          |                                   | --     | 7.3  | --   |       |
| $Q_{gd}$     | Gate to Drain ("Miller")Charge |                                   | --     | 6.5  | --   |       |

**Source-Drain Diode Characteristics**

| Symbol   | Parameter                              | Test Conditions           | Values |      |      | Units |
|----------|----------------------------------------|---------------------------|--------|------|------|-------|
|          |                                        |                           | Min.   | Typ. | Max. |       |
| $I_S$    | Continuous Source Current (Body Diode) | TC=25 °C                  | --     | --   | 7    | A     |
| $I_{SM}$ | Maximum Pulsed Current (Body Diode)    |                           | --     | --   | 28   | A     |
| $V_{SD}$ | Diode Forward Voltage                  | IS=7A,<br>VGS=0V(Note4)   | --     | --   | 1.2  | V     |
| $T_{rr}$ | Reverse Recovery Time                  | IS=7A,<br>Tj = 25°C       | --     | 410  | --   | ns    |
| $Q_{rr}$ | Reverse Recovery Charge                | dIF/dt=100A/us,<br>VGS=0V | --     | 2320 | --   | nC    |

Note1: Pulse width limited by maximum junction temperature

Note2: L=20mH, VDs=50V, Start TJ=25°C

Note3: ISD =7A, di/dt ≤100A/us, VDD≤BVDS, Start TJ=25°C

Note4: Pulse width tp≤300μs, δ≤2%

## 5. Characteristics Curves

Figure 1a Safe Operating Area (No FullPAK)

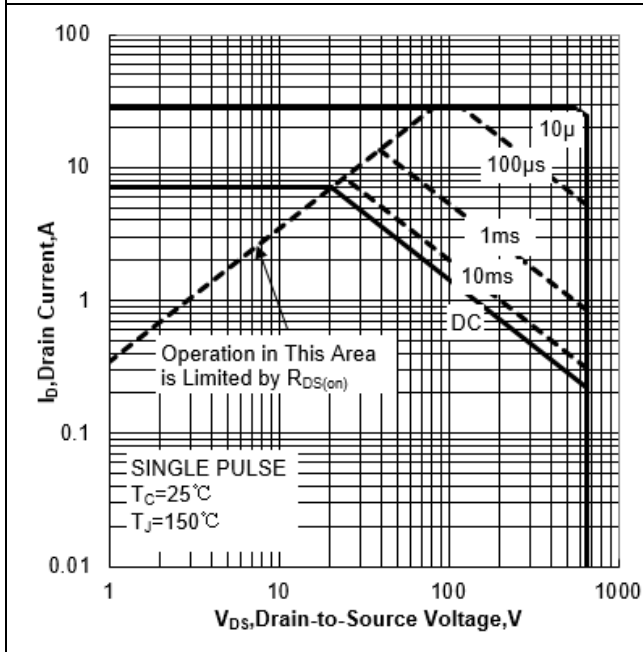


Figure 1b Safe Operating Area (FullPAK)

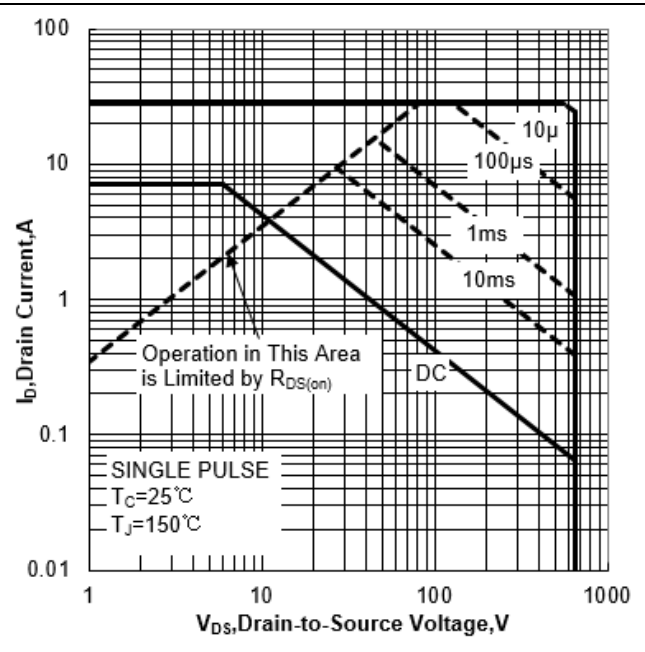


Figure 2a Power Dissipation (No FullPAK)

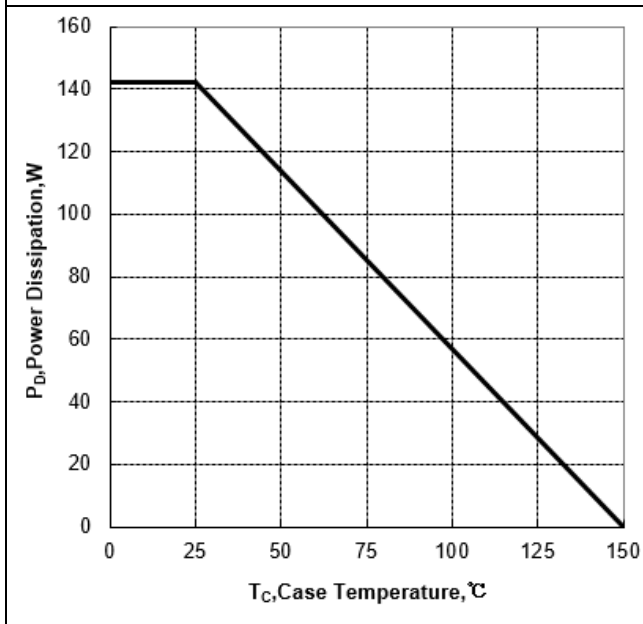


Figure 2b Power Dissipation (FullPAK)

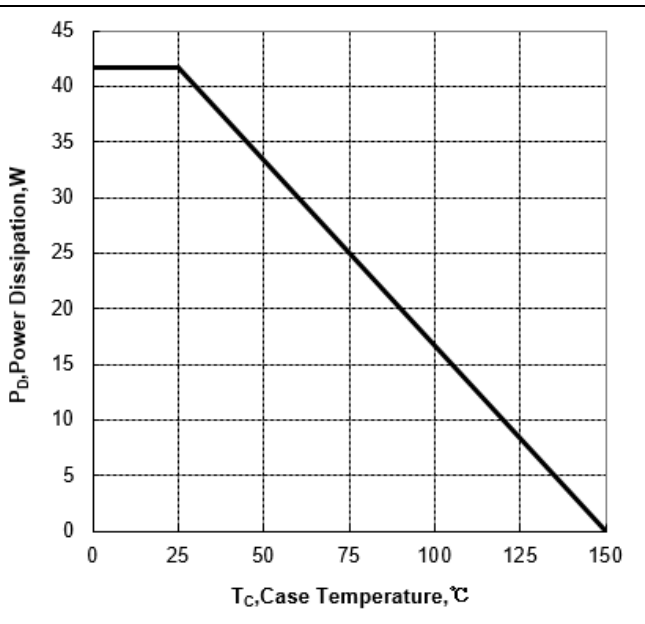


Figure 3a Max Thermal Impedance (No FullPAK)

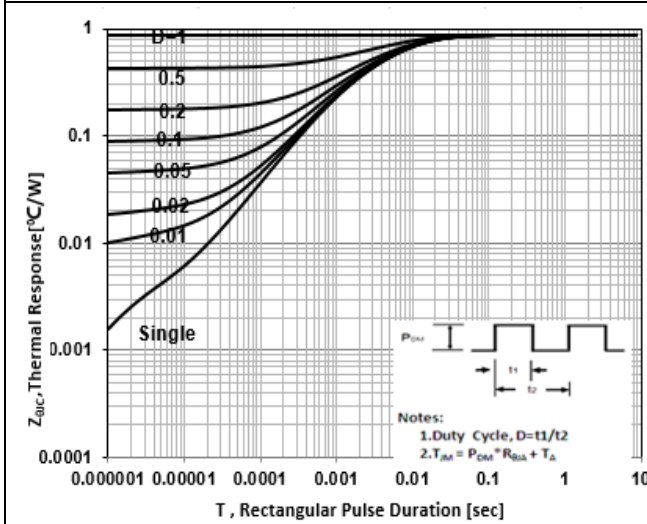


Figure 3b Max Thermal Impedance (FullPAK)

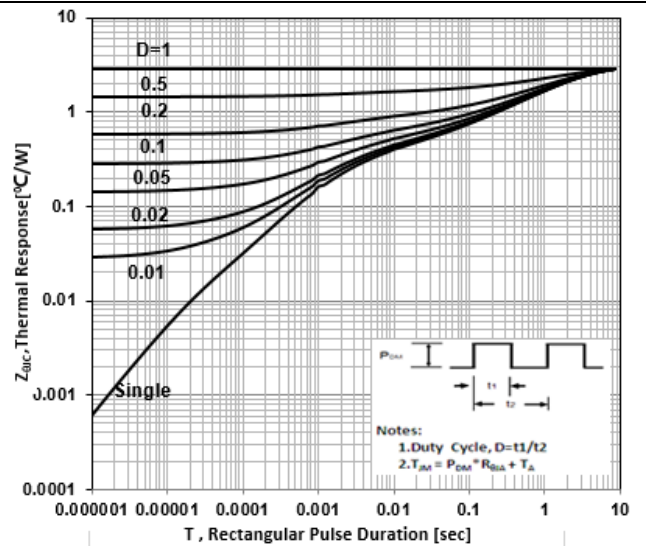


Figure 4 Typical Output Characteristics

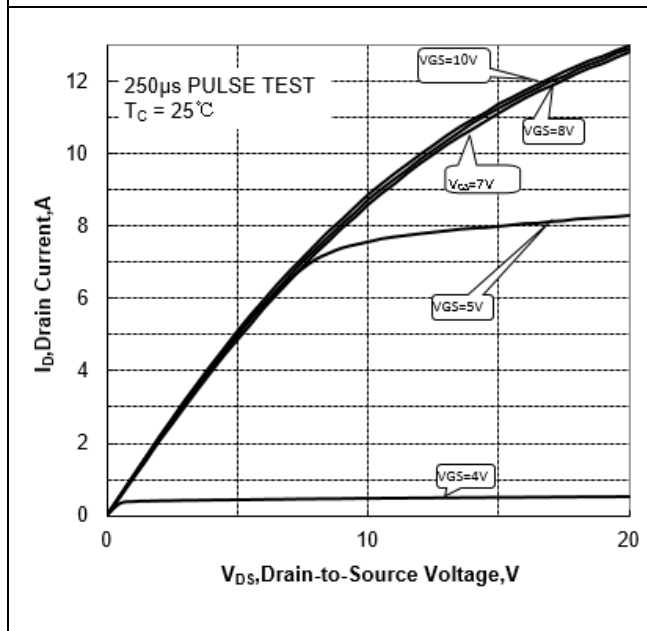
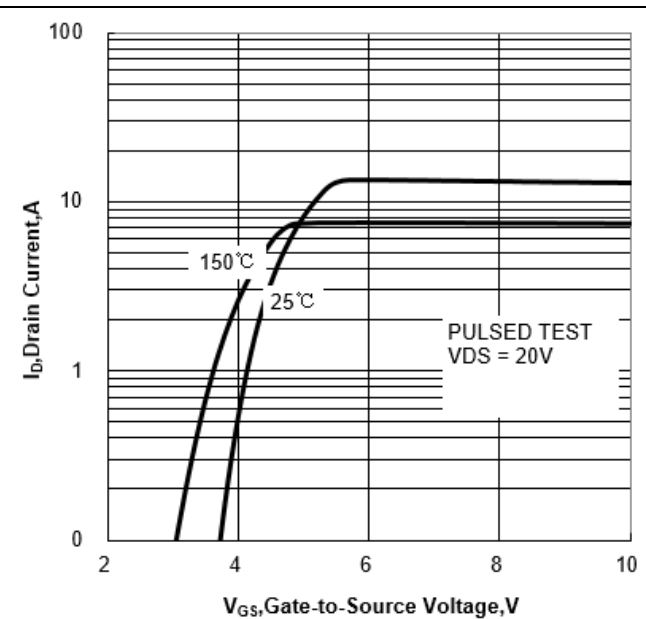
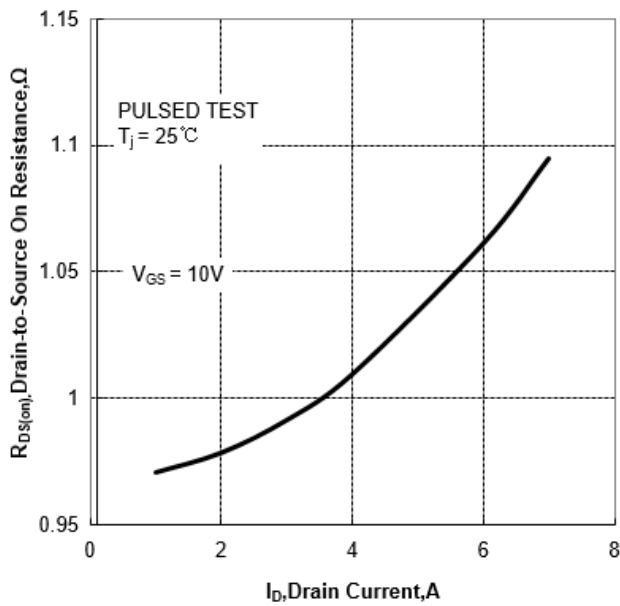


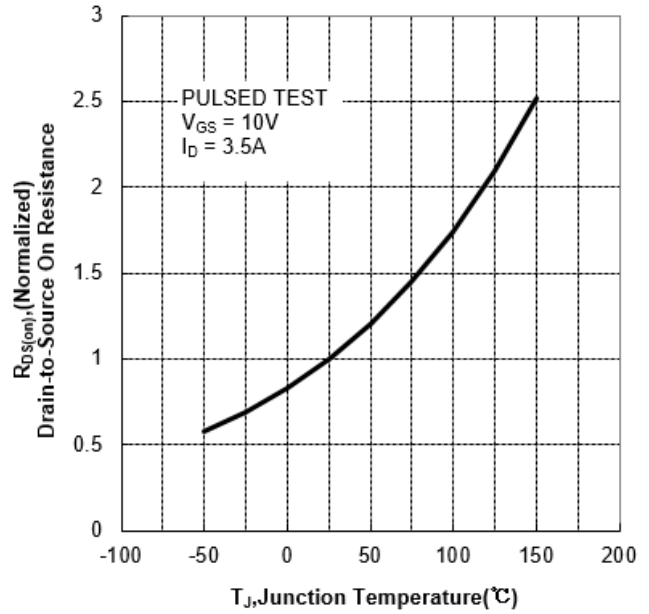
Figure 5 Typical Transfer Characteristics



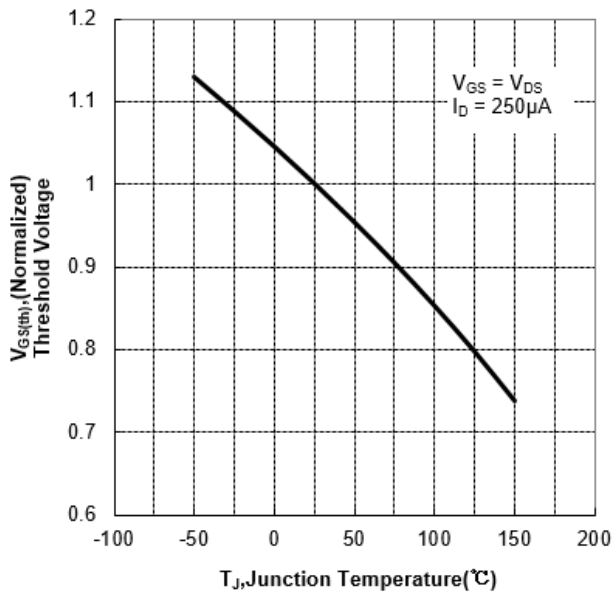
**Figure 6 Typical Drain to Source ON Resistance vs Drain Current**



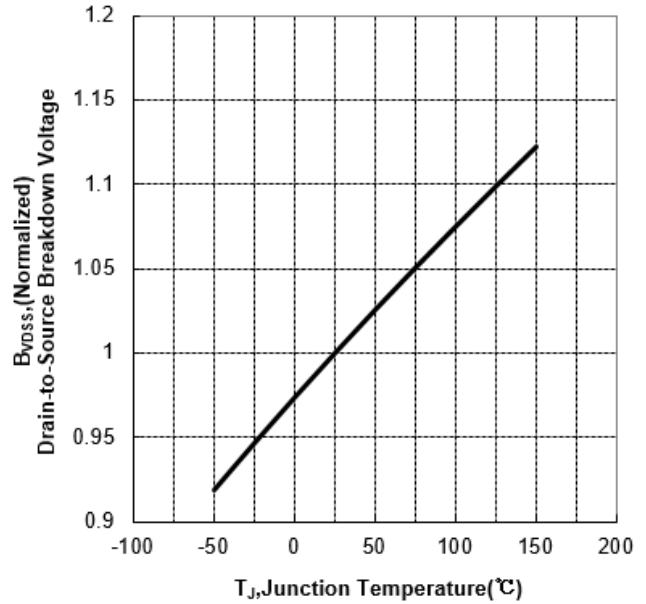
**Figure 7 Typical Drain to Source on Resistance vs Junction Temperature**



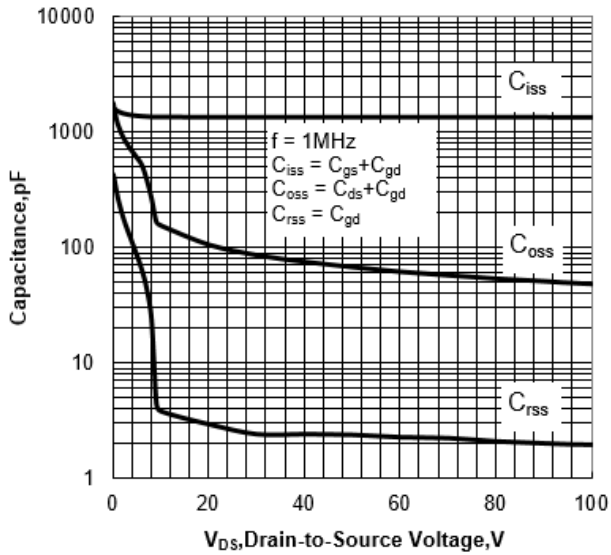
**Figure 8 Typical Theshold Voltage vs Junction Temperature**



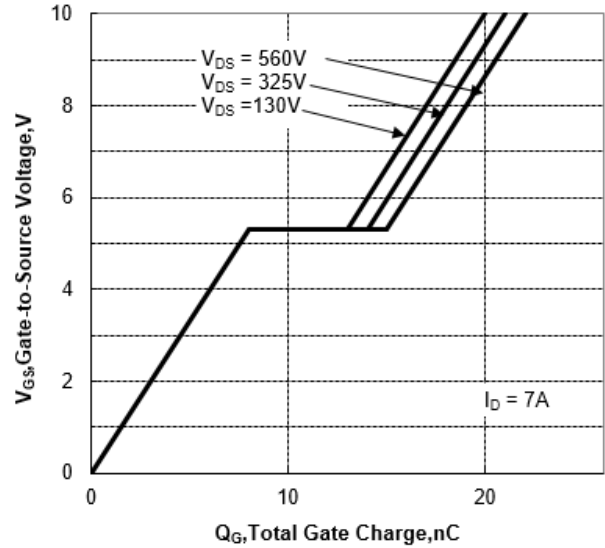
**Figure 9 Typical Breakdown Voltage vs Junction Temperature**



**Figure 10 Typical Capacitance vs Drain to Source Voltage**



**Figure 11 Typical Gate Charge vs Gate to Source Voltage**





## 6. Test Circuit and Waveform

Figure 12 Gate Charge Test Circuit

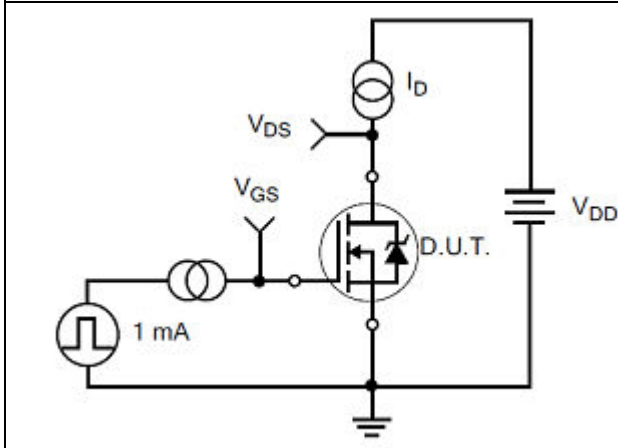


Figure 13 Gate Charge Waveforms

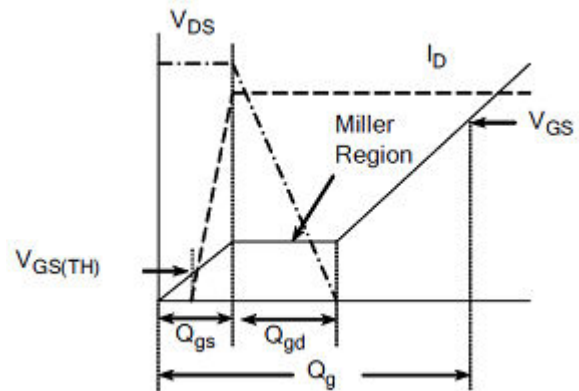


Figure 14 Resistive Switching Test Circuit

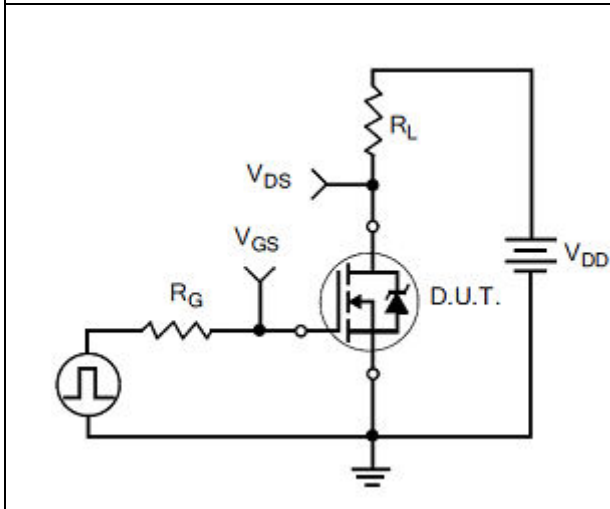


Figure 15 Resistive Switching Waveforms

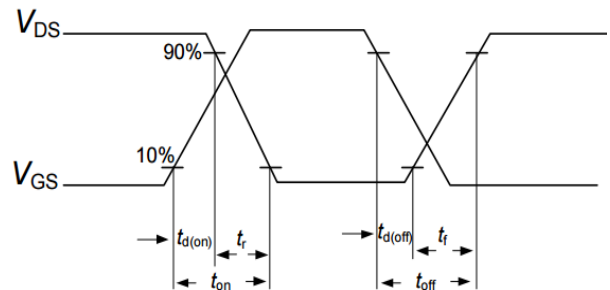


Figure 16 Diode Reverse Recovery Test Circuit

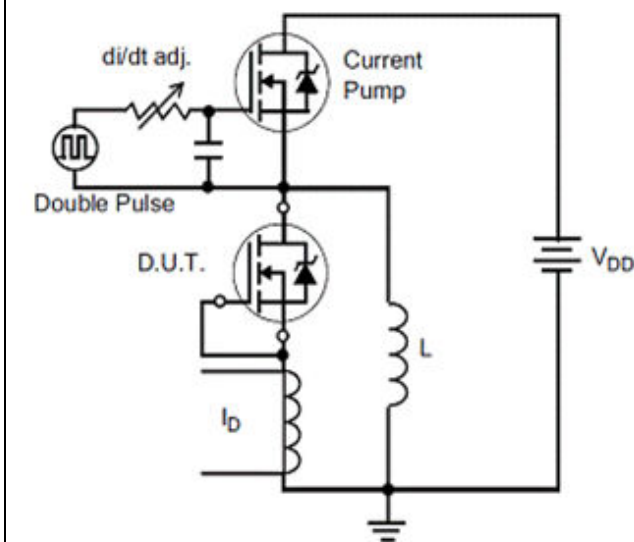


Figure 17 Diode Reverse Recovery Waveform

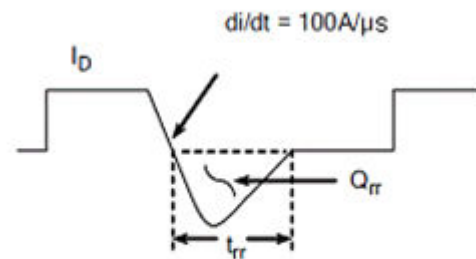


Figure 18 Unclamped Inductive Switching Test Circuit

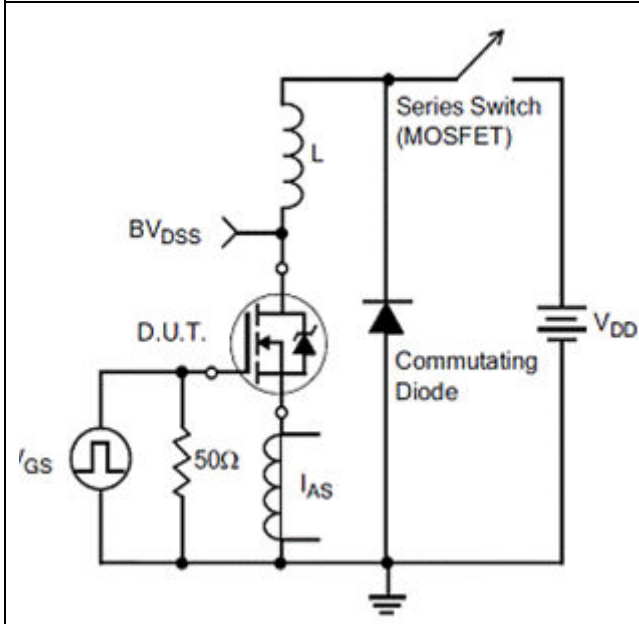
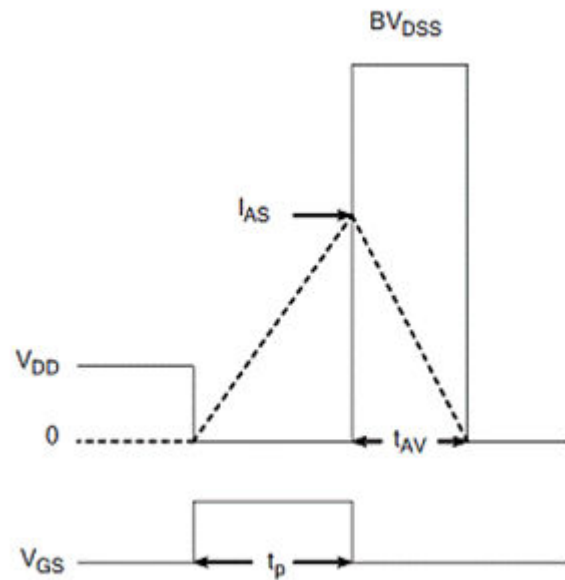
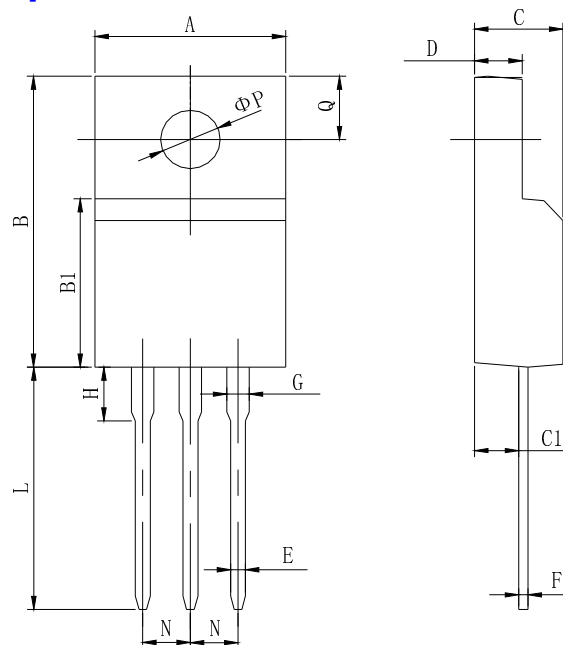


Figure 19 Unclamped Inductive Switching Waveform

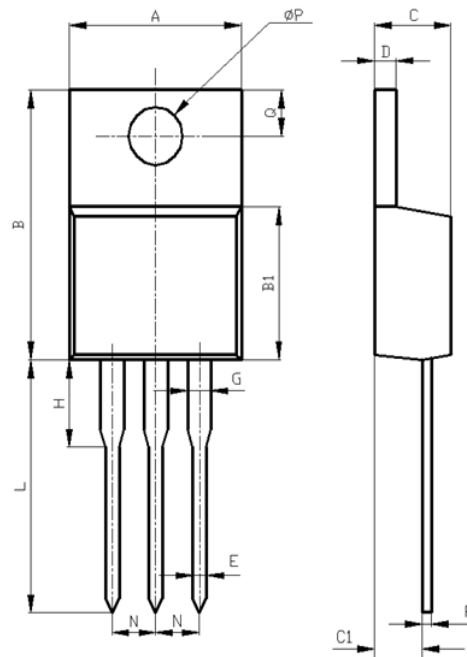


## 7. Package Description



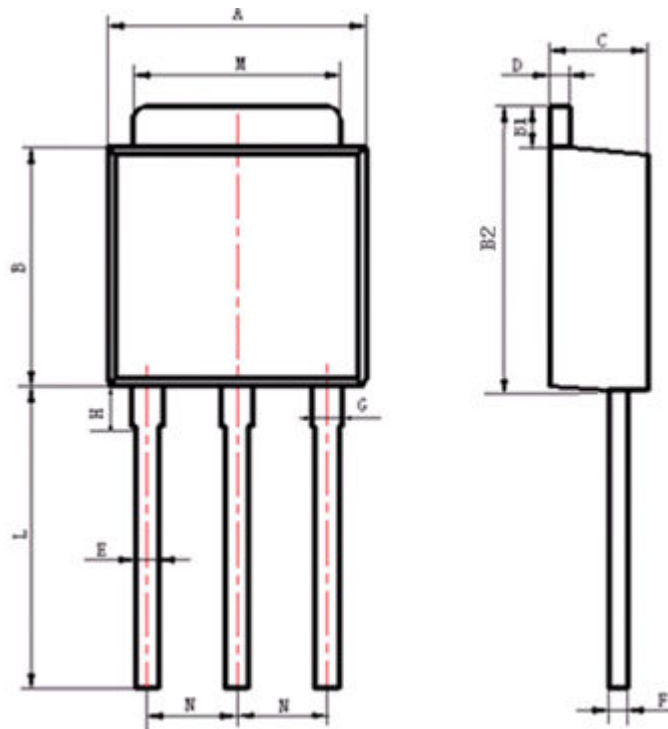
| Items | Values(mm) |      |
|-------|------------|------|
|       | MIN        | MAX  |
| A     | 9.60       | 10.4 |
| B     | 15.4       | 16.2 |
| B1    | 8.90       | 9.50 |
| C     | 4.30       | 4.90 |
| C1    | 2.10       | 3.00 |
| D     | 2.40       | 3.00 |
| E     | 0.60       | 1.00 |
| F     | 0.30       | 0.60 |
| G     | 1.12       | 1.42 |
| H     | 3.40       | 3.80 |
|       | 1.60       | 2.90 |
| L     | 12.0       | 14.0 |
| N     | 2.34       | 2.74 |
| Q     | 3.15       | 3.55 |
| Φ P   | 2.90       | 3.30 |

TO-220F Package



| Items    | Values(mm) |      |
|----------|------------|------|
|          | MIN        | MAX  |
| A        | 9.60       | 10.6 |
| B        | 15.0       | 16.0 |
| B1       | 8.90       | 9.50 |
| C        | 4.30       | 4.80 |
| C1       | 2.30       | 3.10 |
| D        | 1.20       | 1.40 |
| E        | 0.70       | 0.90 |
| F        | 0.30       | 0.60 |
| G        | 1.17       | 1.37 |
| H        | 2.70       | 3.80 |
| L        | 12.6       | 14.8 |
| N        | 2.34       | 2.74 |
| Q        | 2.40       | 3.00 |
| $\phi P$ | 3.50       | 3.90 |

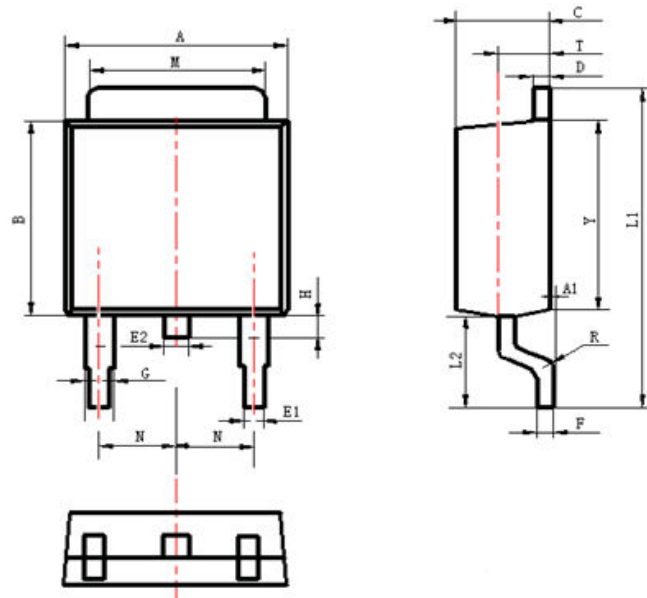
TO-220 Package



| Items | Values(mm) |      |
|-------|------------|------|
|       | MIN        | MAX  |
| A     | 6.30       | 6.90 |
| B     | 5.70       | 6.30 |
| B1    | 1.00       | 1.20 |
| B2    | 6.80       | 7.40 |
| C     | 2.10       | 2.50 |
| D     | 0.30       | 0.60 |
| E     | 0.50       | 0.70 |
| F     | 0.30       | 0.60 |
| G     | 0.70       | 1.00 |
| H     | 1.60       | 2.40 |
| L*    | 3.9        | 4.3  |
| M     | 5.10       | 5.50 |
| N     | 2.09       | 2.49 |

\*: adjustable

TO-251 Package



| Items | Values(mm) |       |
|-------|------------|-------|
|       | MIN        | MAX   |
| A     | 6.30       | 6.90  |
| A1    | 0          | 0.13  |
| B     | 5.70       | 6.30  |
| C     | 2.10       | 2.50  |
| D     | 0.30       | 0.60  |
| E1    | 0.60       | 0.90  |
| E2    | 0.70       | 1.00  |
| F     | 0.30       | 0.60  |
| G     | 0.70       | 1.20  |
| L1    | 9.60       | 10.50 |
| L2    | 2.70       | 3.10  |
| H     | 0.60       | 1.00  |
| M     | 5.10       | 5.50  |
| N     | 2.09       | 2.49  |
| R     | 0.3        |       |
| T     | 1.40       | 1.60  |
| Y     | 5.10       | 6.30  |

TO-252 Package

**NOTE:**

1. Exceeding the maximum ratings of the device in performance may cause damage to the device, even the permanent failure, which may affect the dependability of the machine. Please do not exceed the absolute maximum ratings of the device when circuit designing.
2. When installing the heat sink, please pay attention to the torsional moment and the smoothness of the heat sink.
3. MOSFETs is the device which is sensitive to the static electricity, it is necessary to protect the device from being damaged by the static electricity when using it.
4. Shanghai Belling reserves the right to make changes in this specification sheet and is subject to change without prior notice.

**CONTACT:****上海贝岭股份有限公司（总部）**

地址：上海市宜山路 810 号

邮编：200233

电话：021-24261000

**产品业务咨询及技术支持**

电话：021-24261326

传真 2：021-64852222

邮箱 2：marketing@belling.com.cn

**上海贝岭深圳分公司（华南区）**

地址：深圳市福田区中心区民田路新华保险大厦 1510 室

邮编：518031

电话：0755-33336776 0755-33336770

传真：0755-33336788

**上海贝岭北京办事处（华北区）**

地址：北京市西城区新华里 16 号院锦官苑小区 10 号楼 1 单元 1505 室

邮编：100044

电话：010-64179374

传真：010-8835 9236